N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ZVN0117TA

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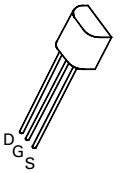
FEATURES

* 170 Volt BV_{DS}

APPLICATIONS

* Telephone handsets



E-Line
TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	170	V
Continuous Drain Current at T_{amb}=25°C	I_D	160	mA
Pulsed Drain Current	I_{DM}	2	A
Gate Source Voltage	V_{GS}	± 20	V
Power Dissipation at T_{amb}=25°C	P_{tot}	700	mW
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	170		V	I_D=10μA, V_{GS}=0V
Gate-Body Leakage	I_{GSS}		100	nA	V_{GS}=± 15V, V_{DS}=0V
Zero Gate Voltage Drain Current	I_{DSS}		10 50	μA μA	V_{DS}=170 V, V_{GS}=0 V_{DS}=140 V, V_{GS}=0V, T=50°C(2)
On-State Drain Current(1)	$I_{D(on)}$	100		mA	V_{DS}=3V, V_{GS}=3.3V
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		23 23	Ω Ω	V_{GS}=3.3V,I_D=100mA V_{GS}=3V,I_D=30mA

(1) Measured under pulsed conditions. Width=300μs. Duty cycle ≤2%